

N-channel TrenchMOS standard level FET Rev. 03 — 7 April 2010

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

#### 1.3 Applications

- 12 V Loads
- Automotive systems

- General purpose power switch
- Motors, lamps and solenoids

#### 1.4 Quick reference data

#### Quick reference data Table 1.

	Quick reference du						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 4</u>	[1]	-	-	75	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	105	W
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;} \\ T_j = 25 \ ^\circ\text{C}\text{; see } \underline{Figure \ 12}\text{;} \\ \text{see } \underline{Figure \ 13} \end{array}$		-	5	7	mΩ
Avalanche	e ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A};  \text{V}_{\text{sup}} \leq 30 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 10  \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $		-	-	198	mJ
Dynamic o	characteristics						
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V};$ $V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 14}{14}$		-	10.7	-	nC

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[1] Continuous current is limited by package.

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

### 3. Ordering information

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
BUK7Y07-30B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

BUK7Y07-30B

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#### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>i</sub> ≥ 25 °C; T <sub>i</sub> ≤ 175 °C		-	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>	<u>[1]</u>	-	-	75	A
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see Figure 1		-	-	63	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 4</u>		-	-	356	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	105	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drai	n diode						
l <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	-	75	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	356	А
Avalanche r	uggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 30 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped \end{array}$		-	-	198	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	see Figure 3	[2][3][4] [5]	-	-	-	J

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

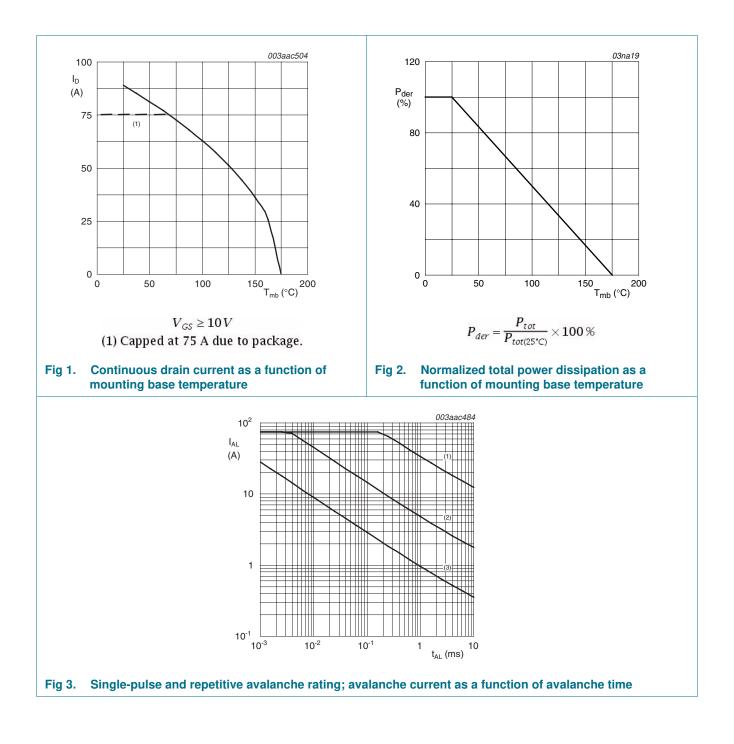
[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[4] Refer to application note AN10273 for further information.

[5] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

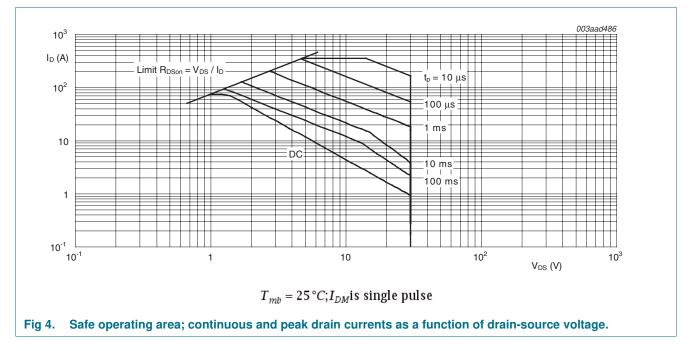
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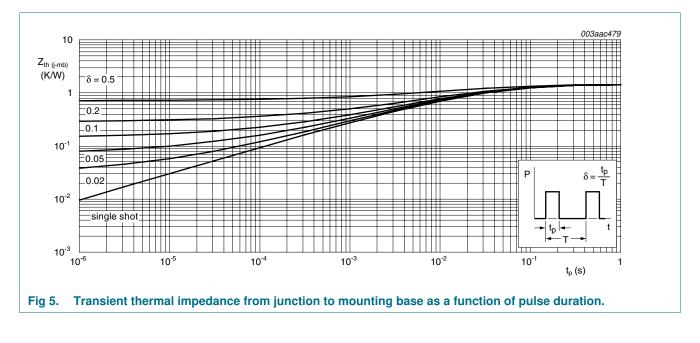
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#### 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	-	1.42	K/W



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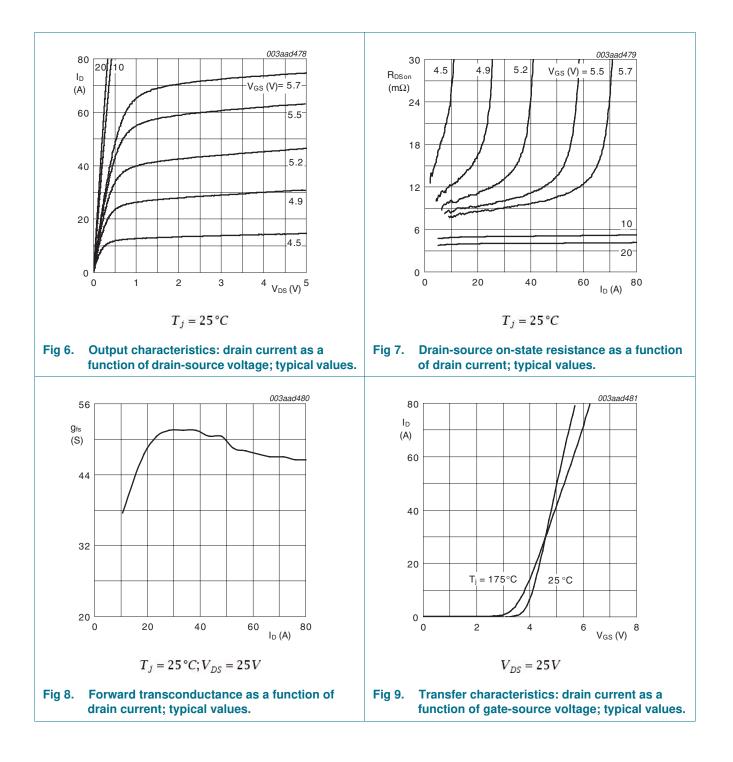
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### 6. Characteristics

Symbol	Doromotor	Conditions	Min	Turn	Mex	ا ا سال
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	30	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	4.4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 10</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 °C$	-	2	100	nA
		V <sub>DS</sub> = 0 V; V <sub>GS</sub> = -20 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12; see Figure 13	-	-	13.4	mΩ
	$V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A}; \text{ T}_j = 25 \text{ °C};$ see Figure 12; see Figure 13	-	5	7	mΩ	
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 10 V;	-	31	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14	-	9.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	10.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	1330	1773	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 15$	-	495	594	pF
C <sub>rss</sub>	reverse transfer capacitance		-	206	282	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	17	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	40	-	ns
t <sub>f</sub>	fall time		-	28	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 16</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; \text{dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{V}_{GS} = 0 \text{ V};$	-	39	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 25 V$	-	53	-	nC

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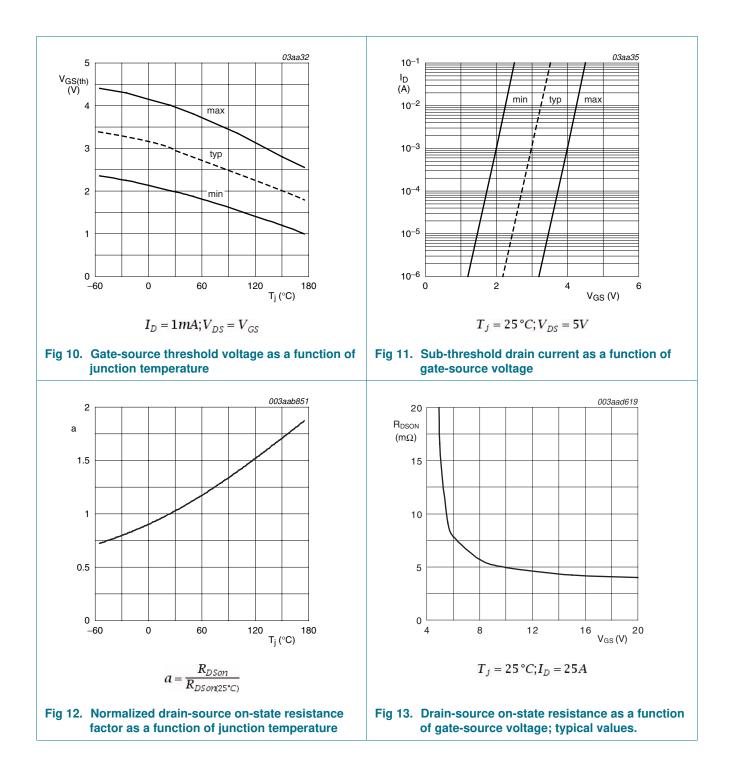
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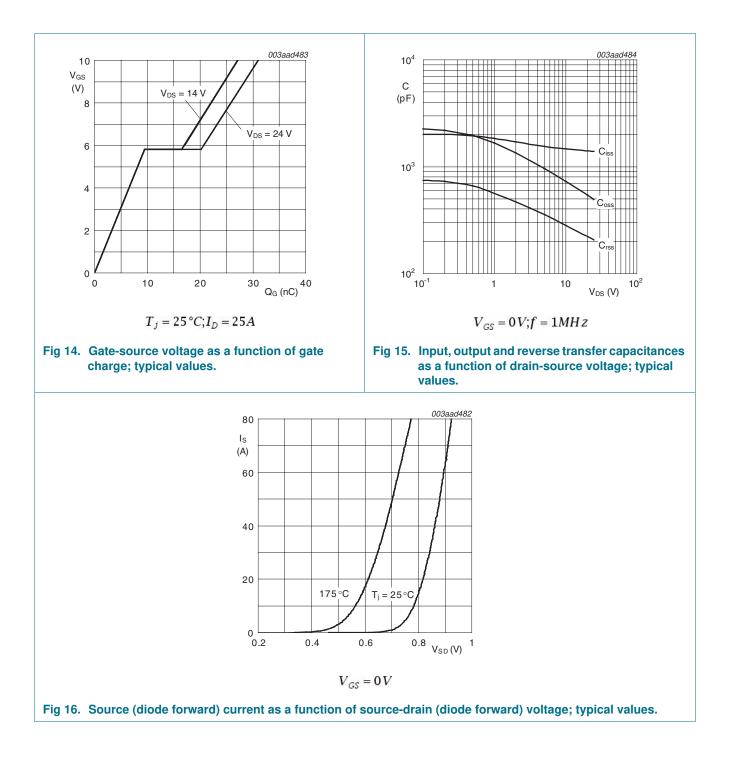


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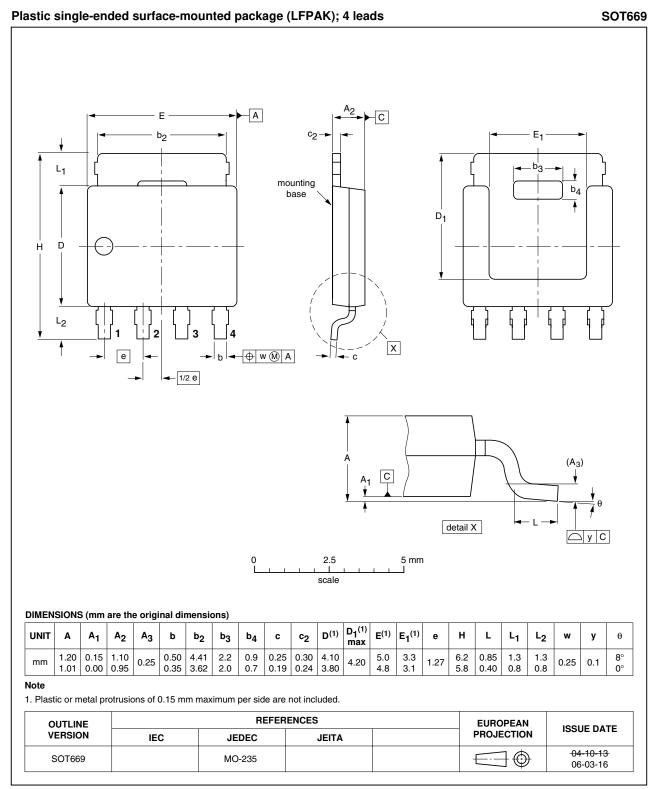
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#### 7. Package outline



#### Fig 17. Package outline SOT669 (LFPAK)

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### 8. Revision history

Table 7.Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y07-30B_3	20100407	Product data sheet	-	BUK7Y07-30B_2
Modifications:	<ul> <li>Status char</li> </ul>	nged from objective to proc	luct.	
BUK7Y07-30B_2	20100215	Objective data sheet	-	BUK7Y07-30B_1

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#### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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